

(12) 按照专利合作条约所公布的国际申请

(19) 世界知识产权组织
国际局



(10) 国际公布号
WO 2026/036603 A1

(43) 国际公布日
2026 年 2 月 19 日 (19.02.2026)

(51) 国际专利分类号:
B28D 5/04 (2006.01)

(21) 国际申请号: PCT/CN2024/139556

(22) 国际申请日: 2024 年 12 月 16 日 (16.12.2024)

(25) 申请语言: 中文

(26) 公布语言: 中文

(30) 优先权:
202411114022.0 2024年8月14日 (14.08.2024) CN

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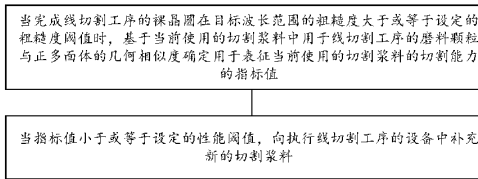
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(54) Title: WAFER AND ROUGHNESS IMPROVEMENT METHOD AND APPARATUS THEREFOR, AND DEVICE AND MEDIUM

(54) 发明名称: 晶圆及其粗糙度的改善方法、装置、设备及介质



S210 When the roughness within a target wavelength range of a bare wafer that has undergone a wire sawing process is greater than or equal to a set roughness threshold, on the basis of the geometric similarity between abrasive particles in the currently used sawing slurry which are used for the wire sawing process and a regular polyhedron, determine an indicator value for representing the sawing capability of the currently used sawing slurry

S220 When the indicator value is less than or equal to a set performance threshold, replenish with a new sawing slurry a device executing the wire sawing process

图 2

(57) Abstract: Provided in the present application are a wafer and a roughness improvement method and apparatus therefor, and a device and a medium. The method comprises: when the roughness within a target wavelength range of a bare wafer that has undergone a wire sawing process is greater than or equal to a set roughness threshold, on the basis of the geometric similarity between abrasive particles in the currently used sawing slurry which are used for the wire sawing process and a regular polyhedron, determining an indicator value for representing the sawing capability of the currently used sawing slurry; and when the indicator value is less than or equal to a set performance threshold, replenishing with a new sawing slurry a device executing the wire sawing process.

(57) 摘要: 本申请提供了一种晶圆及其粗糙度的改善方法、装置、设备及介质; 该方法包括: 当完成线切割工序的裸晶圆在目标波长范围的粗糙度大于或等于设定的粗糙度阈值时, 基于当前使用的切割浆料中用于线切割工序的磨料颗粒与正多面体的几何相似度确定用于表征所述当前使用的切割浆料的切割能力的指标值; 当所述指标值小于或等于设定的性能阈值, 向执行线切割工序的设备中补充新的切割浆料。

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CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN,
TD, TG)。

本国际公布:

— 包括国际检索报告(条约第21条(3))。